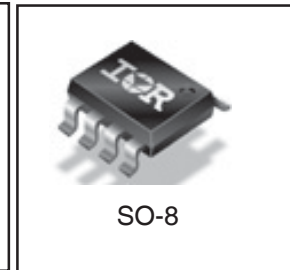
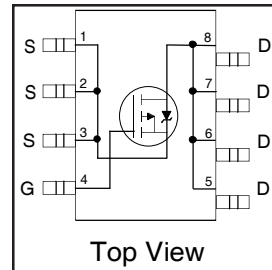


HEXFET® Power MOSFET

V_{DS}	-30	V
$R_{DS(on) \max}$ (@ $V_{GS} = -10V$)	0.07	Ω
$R_{DS(on) \max}$ (@ $V_{GS} = -4.5V$)	0.13	Ω
Q_g (typical)	27	nC
I_D (@ $T_A = 25^\circ C$)	-4.6	A



Features

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification

⇒

Benefits

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7205PbF-1	SO-8	Tube/Bulk	95	IRF7205PbF-1
		Tape and Reel	4000	IRF7205TRPbF-1

Absolute Maximum Ratings

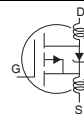
	Parameter	Max.	Units
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	-4.6	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 10V	-3.7	
I_{DM}	Pulsed Drain Current ①	-15	
P_D @ $T_C = 25^\circ C$	Power Dissipation	2.5	W
	Linear Derating Factor	0.020	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	-3.0	V/nS
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance Ratings

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	—	50	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

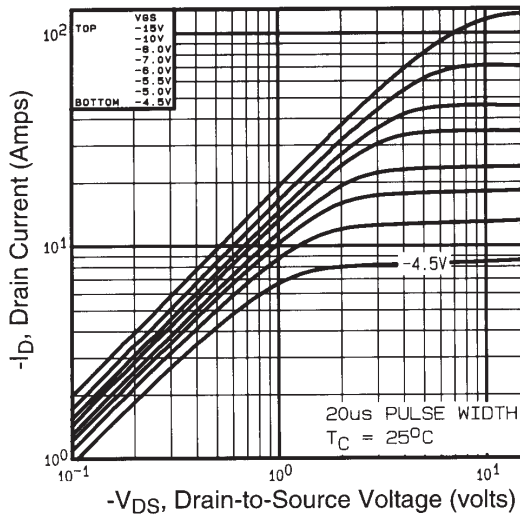
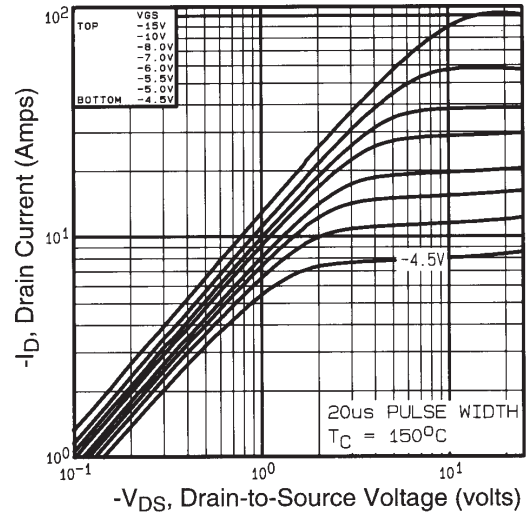
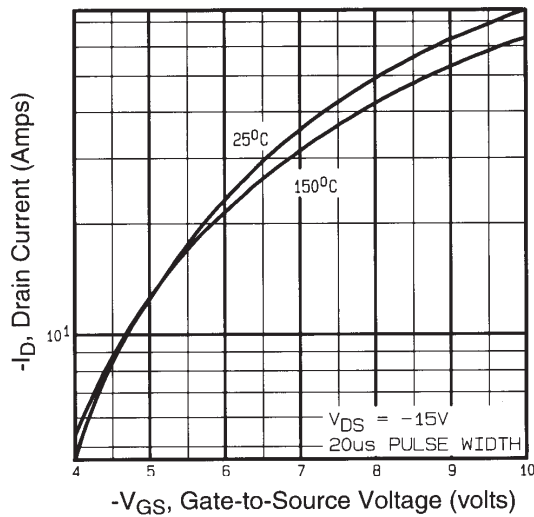
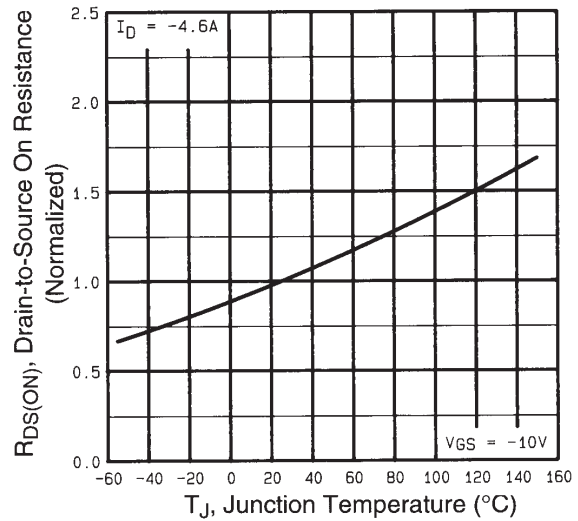
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.024	—	V/°C	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.070 0.130	Ω	$V_{GS} = -10V, I_D = -4.6A$ ③ $V_{GS} = -4.5V, I_D = -2.0A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	—	6.6	—	S	$V_{DS} = -15V, I_D = -4.6A$ ③
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0 -5.0	μA	$V_{DS} = -24V, V_{GS} = 0V$ $V_{DS} = -15V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	27	40	nC	$I_D = -4.6A$
Q_{gs}	Gate-to-Source Charge	—	5.2	—		$V_{DS} = -15V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	7.5	—		$V_{GS} = -10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	14	30	ns	$V_{DD} = -15V$
t_r	Rise Time	—	21	60		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	97	150		$R_G = 6.0\Omega$
t_f	Fall Time	—	71	100		$R_D = 10\Omega$ ③
L_D	Internal Drain Inductance	—	2.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	4.0	—		
C_{iss}	Input Capacitance	—	870	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	720	—		$V_{DS} = -10V$
C_{rss}	Reverse Transfer Capacitance	—	220	—		$f = 1.0\text{MHz}$


Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-15		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.25A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	70	100	ns	$T_J = 25^\circ\text{C}, I_F = -4.6A$
Q_{rr}	Reverse Recovery Charge	—	100	180	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② $I_{SD} \leq -4.6A$, $di/dt \leq 90A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ Surface mounted on FR-4 board, $t \leq 10\text{sec}$.


Fig 1. Typical Output Characteristics,

Fig 2. Typical Output Characteristics,

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

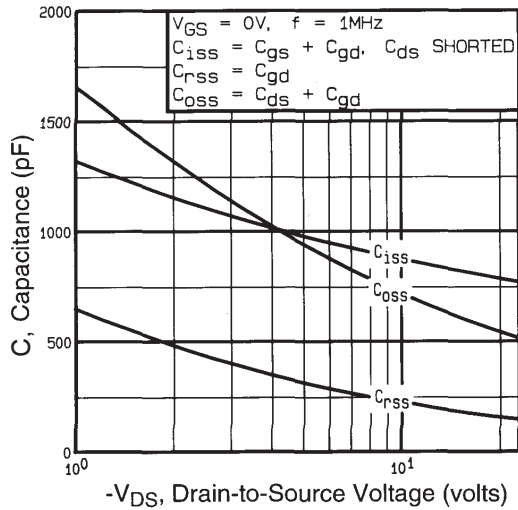


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

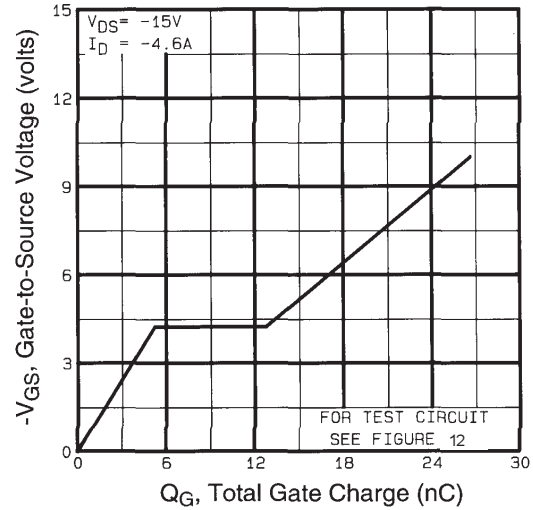


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

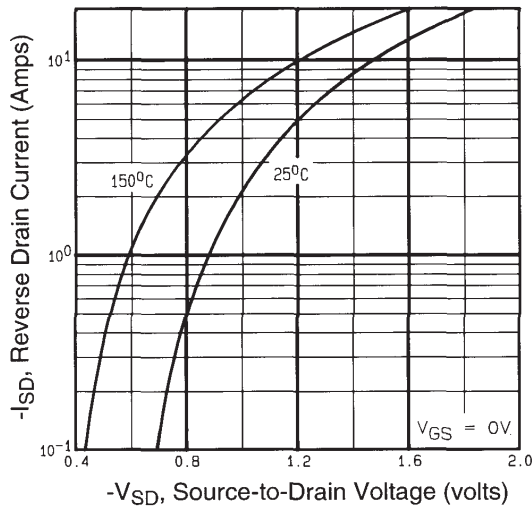


Fig 7. Typical Source-Drain Diode Forward Voltage

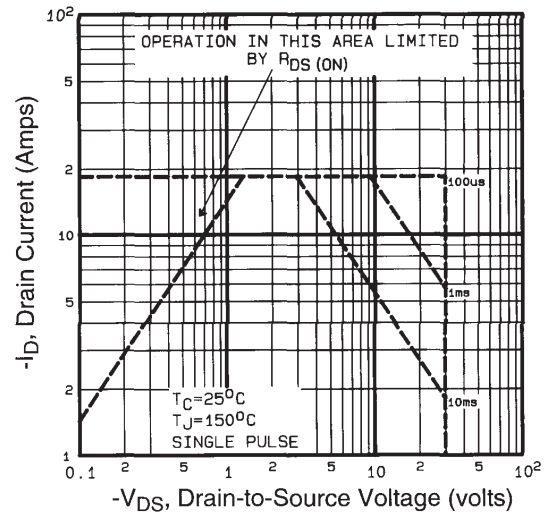


Fig 8. Maximum Safe Operating Area

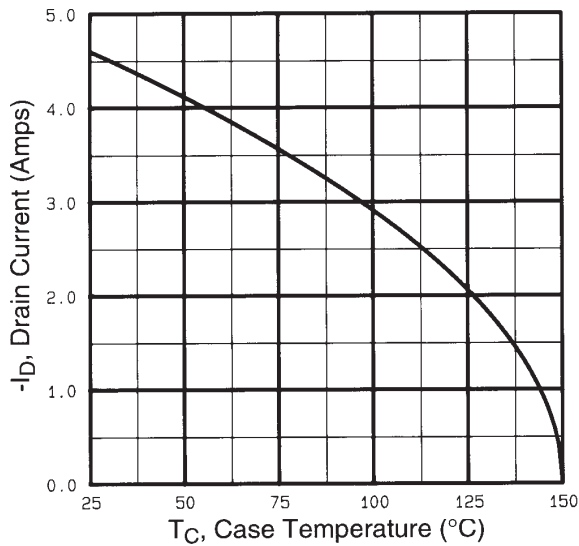


Fig 9. Maximum Drain Current Vs. Case Temperature

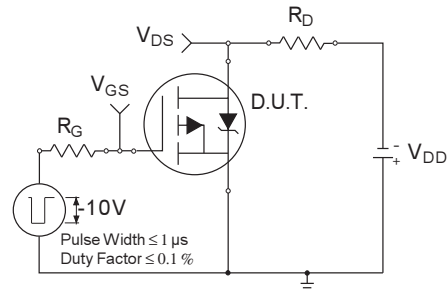


Fig 10a. Switching Time Test Circuit

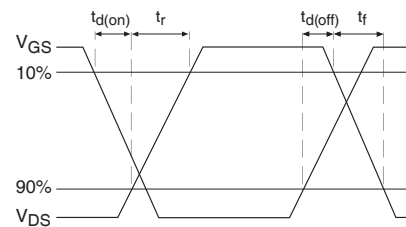


Fig 10b. Switching Time Waveforms

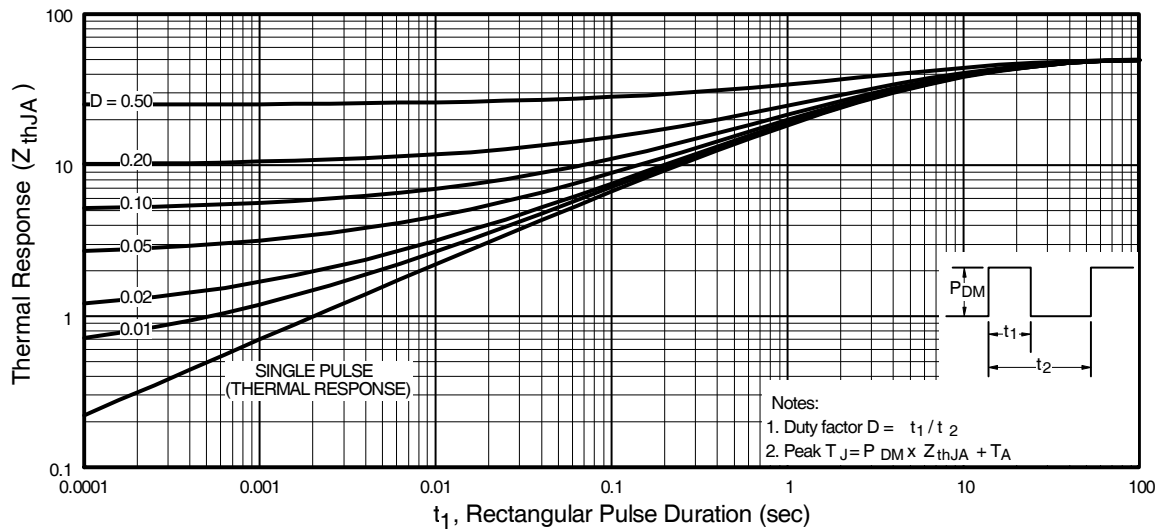
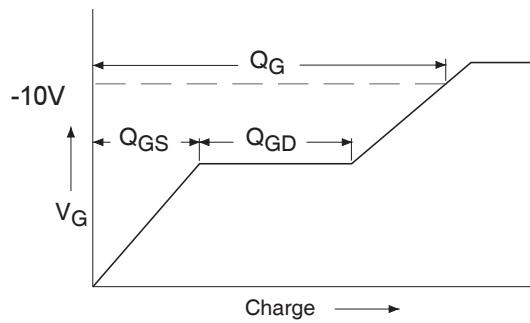
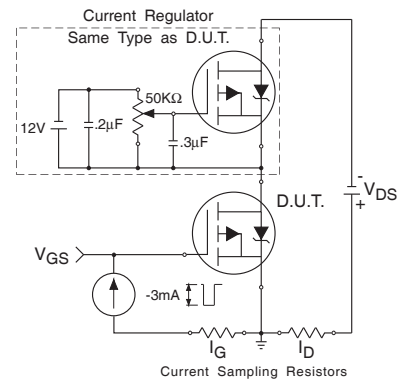
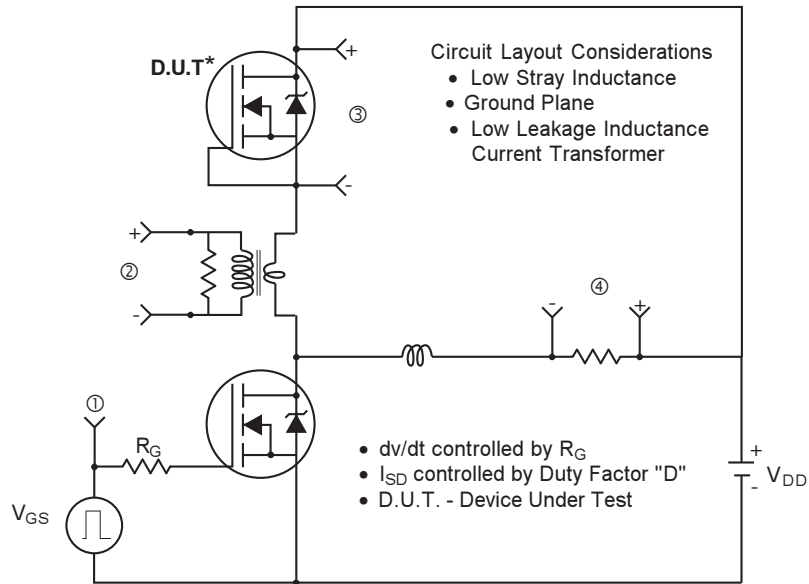


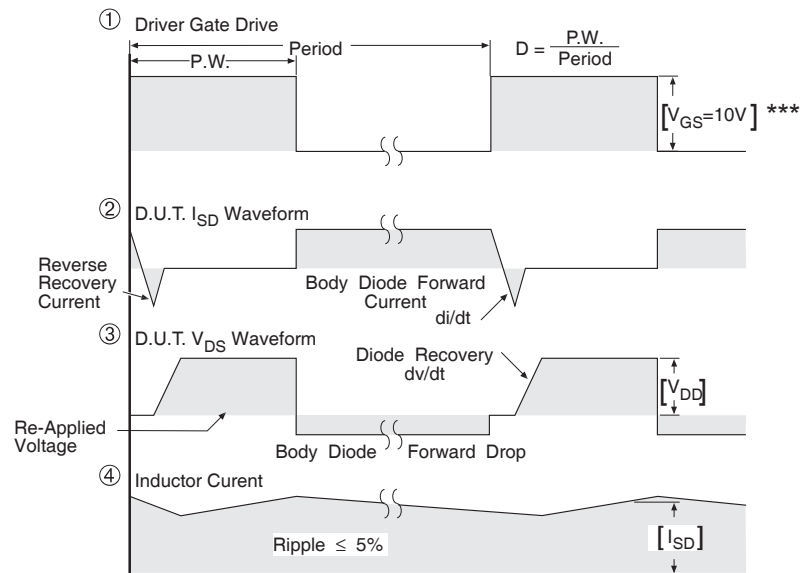
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12a. Basic Gate Charge Waveform

Fig 12b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T. for P-Channel

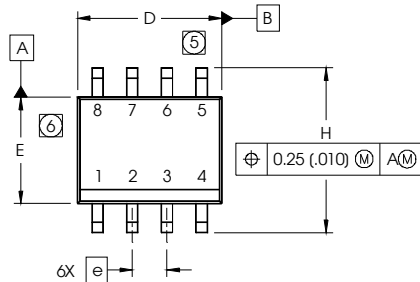


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

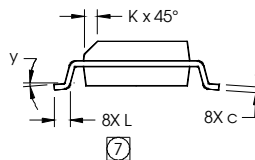
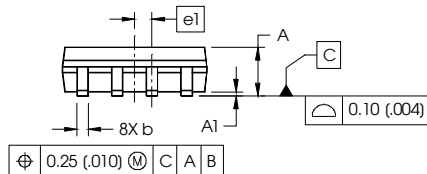
Fig 13. For P-Channel HEXFETS

SO-8 Package Outline (MOSFET & Fetky)

Dimensions are shown in millimeters (inches)



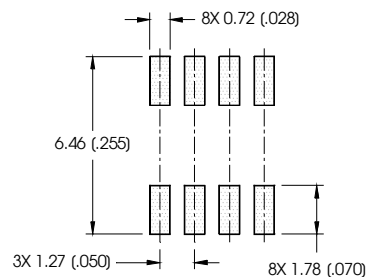
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

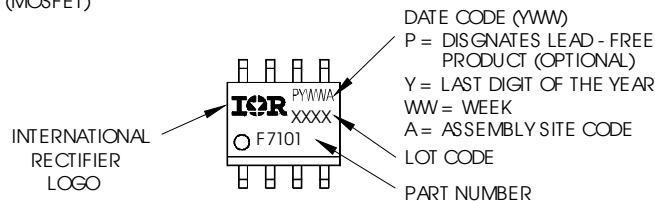
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



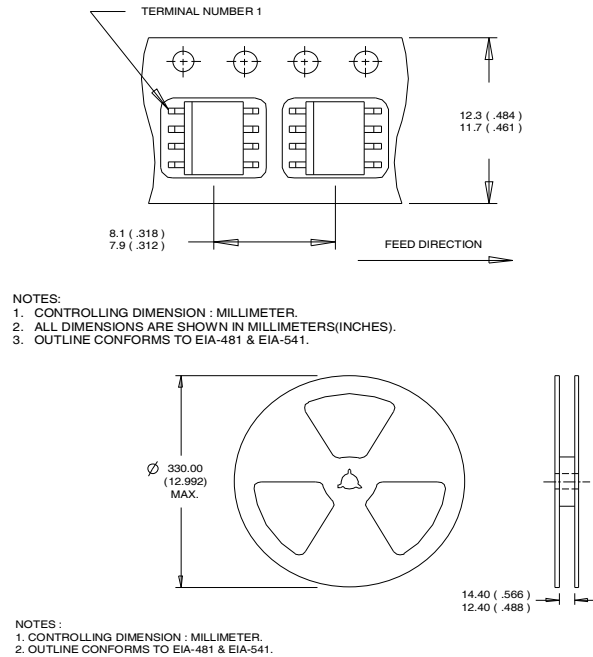
SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification information[†]

Qualification level	Industrial (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>